

Initial Product/Process Change Notification

Document #:IPCN24861X Issue Date:29 Sep 2022

| Title of Change: | NCP1615/NCP1616 re-design from Dual die co-pack (VHVIC3 + ONC25HV) to Single die solution (ONBCD25-UH7) | | | |
|---|---|--|--|--|
| Proposed First Ship date: | 01 Apr 2023 or earlier if approved by customer | | | |
| Contact Information: | Contact your local onse | Contact your local onsemi Sales Office or <u>Jiri.Konarik@onsemi.com</u> | | |
| PCN Samples Contact: | Contact your local onsemi Sales Office. Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements. | | | |
| Type of Notification: | This is an Initial Product/Process Change Notification (IPCN) sent to customers. An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change. In case of questions, contact < < PCN.Support@onsemi.com> | | | |
| Marking of Parts/ Traceability of Change: | Labels on boxes and reels will show "Diffused In: JP" for product produced out of Aizu, Japan. There is no changes to the marking of the actual units. | | | |
| Change Category: | Wafer Fab Change | Wafer Fab Change | | |
| Change Sub-Category(s): | Datasheet/Product Doo | Datasheet/Product Doc change, Manufacturing Site Transfer, Design change | | |
| Sites Affected: | | | | |
| onsemi Sites | | External Foundry/Subcon Sites | | |
| onsemi Aizu, Japan | | None | | |

Description and Purpose:

onsemi would like to inform its customers of a design change to the NCP1615/NCP1616 family of products which are listed in the List of Affected Parts below. This is re-design change from actual dual die co-package solution to single die device solution. Actual VHVIC3 and ONC25HV technologies produced in Gresham, US will be replaced by ONBCD25-UH7 produced in AIZU, Japan.

This design change is intended to improve the overall yield of the product and stabilize our ability to effectively provide product to our customers. While there will be some datasheet changes associated with this that are unavoidable, the product is expected to be a drop-in replacement to the existing design. Customers are highly recommended to request samples to validate any changes. We will not be able to accept any rejections of the FPCN when it is released, as we will not be able to maintain the original product and have to convert to the new design.

| | From | То |
|----------------|-------------|-------------|
| Data sheet | Rev 8 | Rev 9 |
| Wafer Fab Site | Gresham, US | AIZU, Japan |

There are no product material changes as a result of this change.

There is no product marking change as a result of this change.

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Qualification Plan:

QV DEVICE NAME: NCP1615C4DR2G

RMS#: 83464G

PACKAGE: SOIC16 AU MULT HPBF

| Test | Specification | Condition | Interval |
|---------|---------------------|--|------------------------|
| HTOL | JESD22-A108 | Ta=125°C, 100 % max rated Vcc, HV=700V | 1008 hrs |
| HTSL | JESD22-A103 | Ta= 150°C | 1008 hrs |
| PC | J-STD-020 JESD-A113 | MSL1 @ 260 °C | |
| TC | JESD22-A104 | Ta= -65°C to +150°C | 1000 cyc |
| HAST | JESD22-A110 | 130°C, 85% RH, 18.8psig, bias | 192 hrs |
| uHAST | JESD22-A118 | 130°C, 85% RH, 18.8psig, unbiased | 96 hrs |
| BS | AEC-Q100-001 | Cpk 1.67, 30 bonds from 5units | |
| BS | AEC-Q100-001 | Cpk 1.67, 30 bonds from 5units, After TC500/1000 & HAST96/192 | |
| BPS | M883 Method 2011 | 3gm Pull Force Min | |
| BPS | M883 Method 2011 | 3gm Pull Force Min After TC500/1000 & HTSL1008/2016 & HAST96/192 | |
| ESD HBM | AEC-Q100-002 | c = 0, Test @ R | 2kV |
| ESD CDM | AEC-Q100-011 | c = 0, Test @ R | 1kV |
| ED | ON Data Sheet | Cpk > 1.67 Test @ R, H, C | Cpk>1.67 |
| LU | AEC-Q100-004 | Test @ EP; Test & Stress @ R | LU+>100mA LU->100mA |

Estimated date for qualification completion: 1 January 2023

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the <u>PCN Customized Portal</u>.

| Part Number | Qualification Vehicle |
|---------------|-----------------------|
| NCP1616A2DR2G | NCP1615C4DR2G |
| NCP1616A1DR2G | NCP1615C4DR2G |
| NCP1615C5DR2G | NCP1615C4DR2G |
| NCP1615C4DR2G | NCP1615C4DR2G |

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